

2014

M.Sc.

4th Semester Examination

ELECTRONICS

PAPER—ELC-404

Full Marks : 50

Time : 2 hours

The figures in the right-hand margin indicate full marks.

Candidates are required to give their answers in their own words as far as practicable.

Illustrate the answers wherever necessary.

(VLSI Technology)

Answer Q. No. 1 and any three from the rest.

1. (a) What is extrinsic diffusion ?
- (b) Why NMOS are preferred to PMOS in VLSI technology ?
- (c) Mention the merits of utilizing BiCOMs technology in VLSI.
- (d) What do you understand by the functional yield and parametric yield ?
- (e) Draw a cross-sectional view of a buried-channel CCD.

2×5

(Turn Over)

2. (a) Describe with a diagram the various charges associated with thermally oxidized silicon.
- (b) What is the bird's beak structure in the oxidation process? How is it prevented?
- (c) If a silicon oxide of thickness x is grown by thermal oxidation, what is the thickness of silicon being consumed? The molecular weight of Si is 28.9 g mol^{-1} , and the density of Si is 2.33 g cm^{-3} . The corresponding values for SiO_2 are 60.08 g mol^{-1} and 2.21 g cm^{-3} .

$4+(2+1)+3$

3. (a) What are the different lithographic technologies used in VLSI? Make comparisons among them.
- (b) Which type of resist is a better one : a positive resist or a negative resist? Give reasons.
- (c) What is chemical-amplified resist?

$(1+5)+2+2$

4. (a) Explain the circuit shown in Fig. 1 and draw its stick diagram :

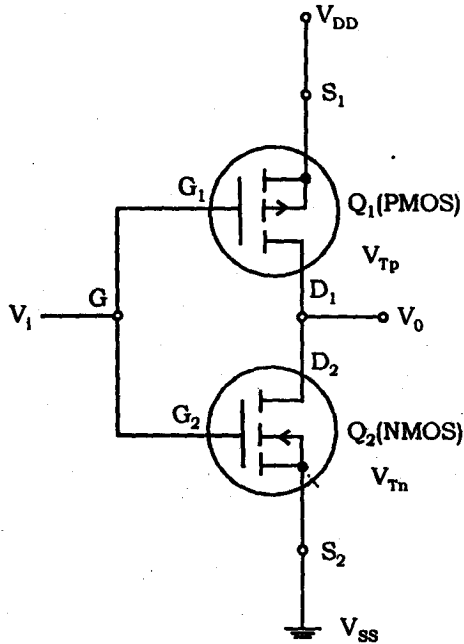


Fig. 1

- (b) Describe the steps involved to fabricate a monolithic integrated circuit of the electrical circuit shown in Fig. 1.

(2+2)+6

5. (a) Why do we scale MOS transistors? Compare between constant voltage scaling and constant electric field scaling.
- (b) A microprocessor was fabricated in a $0.25\ \mu\text{m}$ technology and was able to operate at 100 MHz, consuming 10W using a 2.5V power supply. Using fixed voltage scaling, what will the speed and power consumption of the same processor be if scaled to $0.1\ \mu\text{m}$ technology?
- (c) How does the short channel effect reduce in a recessed-channel MOSFET?

(3+2)+2+3

6. (a) What are the different chip-to-package interconnections used in VLSI? Compare the different attachment methodologies.
- (b) Draw the assembly flow chart for packages using wire.
- (c) Explain the power limitation effect on IC packaging.

(1+4)+3+2

Internal Assessment — 10
